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Sir:

Transmitted herewith for filing under 37 C.F.R. §1.53(b) is a nonprovisional patent application:

For (Title): CHARGE TRANSFER DEVICE, SOLID STATE IMAGE PICKUP DEVICE
USING CHARGE TRANSFER DEVICE, AND CONTROL METHOD FOR
SOLID STATE IMAGE PICKUP DEVICE

By (Inventors): Tetsuo YAMADA

- ☒ 36 pages of Specification/Claims 1-14/Abstract are attached.
- ☒ Formal drawings (Figs. 1-17; 17 sheet(s) is attached.
- ☒ A Declaration and Power of Attorney is attached.
- ☒ An assignment of the invention to Fuji Photo Film Co., Ltd. is attached, along with Form PTO-1595 and a check for \$40.00.
- ☒ Priority of foreign applications Nos. Hei 11-287337 and 2000-287486 filed October 7, 1999 and September 21, 2000 in Japan is claimed under 35 U.S.C. §119.

The filing fee is calculated below and includes claim status after entry of any Preliminary Amendment noted above:

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FOR:	NO. FILED	NO. EXTRA	RATE	FEE		RATE	FEE
BASIC FEE				\$ 355	OR		\$ 710
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INDEP CLAIMS	11 - 3	= 8	x 40 =	\$	OR	x 80	\$ 640
<input type="checkbox"/> MULTIPLE DEPENDENT CLAIMS			+135 =	\$	OR	+270	\$
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- ☒ Check No. 302141 in the amount of \$1,390.00 is attached. Please charge any fee deficiency or credit any overpayment to Deposit Account No. 01-2300.

Respectfully submitted,

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CHARGE TRANSFER DEVICE, SOLID STATE IMAGE PICKUP DEVICE USING
CHARGE TRANSFER DEVICE, AND CONTROL METHOD FOR SOLID STATE
IMAGE PICKUP DEVICE

5 This application is based on Japanese Patent Application HEI 11-
287338, filed on October 7, 1999, and Japanese Patent Application 2000-287486
, filed on September 21, 2000 the entire contents of which are incorporated herein by
reference.

10 BACKGROUND OF THE INVENTION

a) Field of the Invention

The present invention relates to a charge transfer device, a solid state
image pickup device, and a control method for a solid state image pickup device.

b) Description of the Related Art

15 Figs. 15A and 15B show an example of a general charge transfer
device. Fig. 15A is a plan view and Fig. 15B is a schematic cross sectional view.

As shown in Fig. 15B, a charge transfer device X has: a semiconductor
substrate 101 having a principal surface layer of a p-type or an i-type; an n-type
semiconductor layer 105 formed on the surface of the semiconductor substrate 101;
20 charge transfer electrodes 121 of polysilicon formed on an insulating film 115 on the n-
type semiconductor layer 105; and a pulse signal generator 125 for applying pulse
voltages to the charge transfer electrodes.

The charge transfer electrodes 121 include first charge transfer
electrodes 121-1, 121-3, 121-5,... made of first layer polysilicon and second charge
25 transfer electrodes 121-2, 121-4, 121-6,... made of second layer polysilicon. The first

and second charge transfer electrodes are disposed alternately in a horizontal direction.

The regions of the n-type semiconductor layer 105 under the first charge transfer electrodes 121-1, 121-3, 121-5,... made of the first layer polysilicon have a low n-type impurity concentration, forming potential barriers (B). The regions of the n-type semiconductor layer 105 under the second charge transfer electrodes 121-2, 121-4, 121-6,... made of the second layer polysilicon have a high n-type impurity concentration, forming potential wells (W).

First and second two charge transfer electrodes 121 adjacent to each other in the horizontal direction, e.g., the first and second charge transfer electrodes 121-1 and 121-2, or 121-3 and 121-4, are connected in common. A pulse signal $\Phi 2$ is applied from the pulse signal generator 125 to the commonly connected charge transfer electrodes 121-1 and 121-2. A pulse signal $\Phi 1$ is applied from the pulse signal generator 125 to the commonly connected charge transfer electrodes 121-3 and 121-4.

Similarly, pairs of first and second two adjacent charge transfer electrodes disposed alternately in the horizontal direction are alternately applied with pulse signals $\Phi 2$, $\Phi 1$, $\Phi 2$, $\Phi 1$,... from the pulse signal generator 125.

Fig. 16 shows the waveforms of pulse signals generated from the pulse signal generator 125 (Fig. 15B).

The pulse signal $\Phi 1$ has a waveform with a low level and a high level being set alternately. The pulse signal $\Phi 2$ has a waveform opposite in phase to the pulse signal $\Phi 1$.

As the pulse signals $\Phi 1$ and $\Phi 2$ are applied to the charge transfer device X shown in Figs. 15A and 15B, charges are transferred in the horizontal

direction by a two-phase drive method as shown in Fig. 15B.

In addition to the two-phase drive method, charges may be transferred by a three-phase drive method, a four-phase drive method or the like.

In the charge transfer device of a two-phase drive type, a pair of first and second two charge transfer electrodes 121 constitutes one charge transfer stage. In the charge transfer device of the two-phase drive type described above, each charge transfer stage is fixed.

Fig. 17 is a plan view showing a solid state image pickup device A using the charge transfer device X shown in Figs. 15A and 15B.

The solid state image pickup device A shown in Fig. 17 has: a plurality of photoelectric conversion elements 103 disposed regularly on a two-dimensional plane of the surface of a semiconductor substrate 101; a plurality of vertical charge transfer paths 105 for reading signal charges accumulated in the photoelectric conversion elements 103 and sequentially transferring the read charges in a column direction; a horizontal charge transfer path 107 connected to one ends of the vertical charge transfer paths 105 for transferring charges transferred from the vertical charge transfer paths 105 in the horizontal direction; and an output amplifier 111 for amplifying the charges transferred from the horizontal charge transfer path 107 and outputting the amplified charges.

A read gate 103a is formed between the photoelectric conversion element 103 and vertical charge transfer path 105 to read charges accumulated in the photoelectric conversion element 103 to the vertical charge transfer path 105. Charges are transferred in the vertical charge transfer path 105 toward the horizontal charge transfer path 107.

The charge transfer device X is used as the horizontal charge transfer

path 107.

One end of the vertical charge transfer path 105 is connected to the high concentration n-type semiconductor layer 105a forming a well layer in the horizontal charge transfer path 107.

5 The two-phase drive type charge transfer device described above is driven by two-phase drive pulses. Conventional three-phase or four-phase drive type charge transfer devices not using barrier layers and well layers transfer charges by three-phase or four-phase drive pulses, and cannot transfer charges by different methods.

10 For example, in the two-phase drive type charge transfer device, two charge transfer electrodes constitute one charge transfer stage and a geometrical length of one charge transfer stage is fixed. Such constriction poses some problem when the charge transfer device is used as the horizontal charge transfer path of a solid state image pickup device. Specifically, in a solid state image pickup device, one
15 charge transfer stage of the horizontal charge transfer path is provided for each vertical charge transfer path in order to transfer all image signals from the vertical charge transfer paths to the horizontal charge transfer path.

In an image monitor mode, it is desired to reproduce an image at high speed by thinning the number of read pixels. It is also desired to thin the numbers of
20 both rows and columns. In this case, if signal charges (electrons) are transferred only in even columns, signal charges are stored in the transfer stages of every second even columns, and charges are not stored in the transfer stages in odd columns adjacent in the horizontal direction so that the transfer stages are empty. This
horizontal charge transfer path processes both an image signal and an empty signal,
25 and transfers even an empty charge as a signal.

Therefore, even if the number of signal bits is reduced, a substantial data rate of the horizontal charge transfer path of a solid state image pickup device does not lower nor a consumption power reduces.

5 SUMMARY OF THE INVENTION

It is an object of the present invention to provide a solid image pickup device using a charge transfer device which can raise a data rate and reduce a consumption power by changing the number of charge transfer stages with the number of signal bits.

10 According to one aspect of the present invention, there is provided a charge transfer device comprising: a semiconductor substrate; a charge transfer path formed in the semiconductor substrate and made of a first conductivity type semiconductor layer; a plurality of charge transfer electrodes formed near above the charge transfer path; and a first pulse signal generator circuit for applying either a first
15 pulse signal train for n-phase (n being an integer larger than 1) driving of charges in the charge transfer path to the charge transfer electrodes or a second pulse signal train for (n + 1)-phase driving of charges in the charge transfer path to the charge transfer electrodes.

According to another aspect of the present invention, there is provided a
20 method of reading a solid state image pickup device, the solid state image pickup device including: a semiconductor substrate; a plurality of photoelectric conversion elements regularly disposed in row and column directions on the semiconductor substrate; a plurality of vertical charge transfer paths extending in a vertical direction and each disposed adjacent to each of a plurality of photoelectric conversion element
25 columns regularly disposed in the column direction; a read gate formed between each

photoelectric conversion element and a corresponding vertical charge transfer path for transferring charges accumulated in the photoelectric conversion element to the vertical charge transfer path; a horizontal charge transfer path formed at one ends of the plurality of vertical charge transfer paths for transferring charges in a horizontal direction; and an output amplifier for amplifying charges transferred by the horizontal charge transfer path and outputting the amplified charges, the horizontal charge transfer path including: a charge transfer path formed in the semiconductor substrate and made of a first conductivity type semiconductor layer, the charge transfer path having first barrier layers having a high potential and second well layers having a low potential, disposed alternately; a plurality of first and second charge transfer electrodes alternately formed near above the first barrier layers and first well layers of the charge transfer path; a plurality of charge transfer electrode pairs each having adjacent first and second two charge transfer electrodes connected together; and a third pulse signal generator circuit for applying either a fourth pulse signal train of two-phase for 2-phase driving of charges in the charge transfer path to two charge transfer electrode pairs or a fifth pulse signal train for 2k-phase driving or more of charges in the charge transfer path to the charge transfer electrode pairs, the method comprising: either a step of, when charges accumulated in all photoelectric conversion elements are read, transferring charges in the horizontal charge transfer path by a two-phase drive method; or a step of executing a 1/k horizontal thinning operation by selectively reading charges from photoelectric conversion elements adjacent in the horizontal direction of one column per k columns and transferring charges in the horizontal charge transfer path by a 2k-phase drive method.

As above, a length of one charge transfer stage of a charge transfer device can be changed with the phase of drive pulses.

A monitor image taking operation of an electronic still camera, such as 1/2, 1/3 and 1/4 thinning operations, can be realized without empty charge transfer so that a consumption power can be reduced.

It is possible to raise the data rate and display a monitor image of a high
5 quality with a low consumption power.

A capacity of signal transfer can be increased greatly by a multiple-phase drive method.

BRIEF DESCRIPTION OF THE DRAWINGS

10 Fig. 1 is a plan view of a charge transfer device according to a first embodiment of the invention.

Fig. 2 shows a cross sectional structure of the charge transfer device shown in Fig. 1, with illustrations how charges are transferred.

15 Fig. 3 shows the waveforms of drive pulses applied to horizontal charge transfer electrodes during a charge transfer of the charge transfer device.

Fig. 4 shows a cross sectional structure of a charge transfer device according to a second embodiment of the invention, with illustrations how charges are transferred.

20 Fig. 5 shows the waveforms of drive pulses applied to horizontal charge transfer electrodes during a charge transfer of the charge transfer device of the second embodiment.

Fig. 6 is a plan view of a charge transfer device according to a third embodiment of the invention.

25 Fig. 7 shows a cross sectional structure of the charge transfer device shown in Fig. 6, with illustrations how charges are transferred.

Fig. 8 shows the waveforms of drive pulses applied to horizontal charge transfer electrodes during a charge transfer of the charge transfer device.

Fig. 9 is a plan view of a solid state image pickup device according to a fourth embodiment of the invention.

5 Fig. 10 is a plan view of a solid state image pickup device according to a modification of the fourth embodiment and illustrates a thinning read operation.

Fig. 11 is a plan view of a solid state image pickup device according to a fifth embodiment of the invention and illustrate a charge read method.

10 Fig. 12 shows the waveforms of drive pulses applied to horizontal charge transfer electrodes during a charge read operation of the charge transfer device shown in Fig. 11.

Fig. 13 is a plan view of a solid state image pickup device according to a modification of the fifth embodiment and illustrates a thinning charge read operation.

15 Fig. 14 shows the waveforms of drive pulses applied to horizontal charge transfer electrodes during a charge read operation of the charge transfer device shown in Fig. 13.

Fig. 15A is a plan view of a conventional two-phase drive type charge transfer device, and Fig. 15B is a diagram showing the cross section thereof and illustrating how charges are transferred.

20 Fig. 16 shows the waveforms of pulse signals applied to a conventional two-phase drive type charge transfer device.

Fig. 17 is a plan view of a conventional solid state image pickup device.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

25 A charge transfer device according to the first embodiment of the

invention will be described with reference to Fig. 1, Figs. 2A and 2B and Fig. 3.

Fig. 1 is a plan view of the charge transfer device of the first embodiment, Fig. 2 shows a cross sectional structure of the charge transfer device, with illustrations how charges are transferred. Fig. 3 shows the waveforms of drive pulses.

As shown in Figs. 1, 2, a charge transfer device A has: a semiconductor substrate 1; a first conductivity type (n-type) semiconductor layer 7 formed on the surface of the semiconductor substrate 1; charge transfer electrodes 21 of polysilicon formed on an insulating film 15 on the semiconductor layer 7; and pulse signal generators 25 (25a, 25b) for applying pulse voltages to the charge transfer electrodes.

The charge transfer electrodes 21 include generally first charge transfer electrodes 21-1, 21-3, 21-5,... made of first layer polysilicon and second charge transfer electrodes 21-2, 21-4, 21-6,... made of second layer polysilicon. The first and second charge transfer electrodes are disposed alternately in a horizontal direction.

The n-type semiconductor layer 7 has an approximately uniform thickness, forming impurity doped regions.

Eight charge transfer electrodes 21 adjacent to each other in the horizontal direction, e.g., the electrodes 21-1 to 21-8, form one charge transfer electrode group G1.

A pulse signal $\Phi 1$ is applied from the pulse signal generator 25 (25a) to the charge transfer electrode 21-1. A pulse signal $\Phi 2$ is applied from the pulse signal generator 25 (25a) to the charge transfer electrode 21-2 adjacent to the charge transfer electrode 21-1. A pulse signal $\Phi 3$ is applied from the pulse signal generator 25 (25a) to the charge transfer electrode 21-3 adjacent to the charge transfer electrode 21-2. A pulse signal $\Phi 4$ is applied from the pulse signal generator 25 (25a)

to the charge transfer electrode 21-4 adjacent to the charge transfer electrode 21-3.

Similarly, the pulse signals $\Phi 1$ to $\Phi 4$ are applied to the adjacent charge transfer electrodes 21-5 to 21-8.

The pulse signals $\Phi 1$ to $\Phi 4$ are called a first pulse signal train.

5 Different pulse signals $\Phi 1$ to $\Phi 8$ are applied from the pulse signal generator 25 (25b) to the same charge transfer electrodes 21 of the charge transfer electrode group G1.

The pulse signals $\Phi 1$ to $\Phi 8$ are called a second pulse signal train.

10 As the first pulse signal train (four-phase drive pulses) is applied to the transfer electrodes 21 of the charge transfer device A, charges in the charge transfer device are transferred by a four-phase drive method.

In addition to the four-phase drive method, an n-phase (n is an integer larger than 2) drive method such as a two-phase or a three-phase drive method may be used.

15 As the second pulse signal train (eight-phase drive pulses) is applied to the transfer electrodes 21 of the charge transfer device A, charges in the charge transfer device are transferred by an eight-phase drive method.

The length of a charge transfer stage for the eight-phase drive method by applying the second pulse signal train is two times that for the four-phase drive method by applying the first pulse signal train. As applying the first pulse signal train, the length of a charge transfer stage for an n-phase drive method (n is a positive integer) is $n/4$ times that for the four-phase drive method.

In addition to the eight-phase drive method, an $(n + 1)$ -phase or $(n \times m)$ -phase drive method may be used (m is an integer larger than 1).

25 Fig. 3 shows the voltage waveforms of the second pulse signal train

generated by the pulse signal generator 25.

The drive pulses $\Phi 1$ to $\Phi 8$ rise from the low level to the high level and fall from the high level to the low level, in the sequential order of $\Phi 1$ to $\Phi 8$, as seen along the abscissa (time) in Fig. 3.

5 Fig. 2 shows the charge distribution in the charge transfer device A at times t_1 , t_2 and t_3 shown in Fig. 3. Charge signals transferred from the vertical charge transfer paths are transferred in the horizontal direction sequentially from time t_1 to time t_3 . As compared to a conventional two-phase charge transfer, a ratio of empty charge transfer stages to total stages is low. The charge transfer efficiency is
10 therefore improved. Since eight charge transfer electrodes are driven during one period, a charge transfer is speeded up.

The pulse signal generators for generating the first and second pulse signal trains may be formed in the same circuit or in separate circuits. The pulse signal generators may be formed in the same semiconductor substrate or in different
15 substrates (chips).

Figs. 4A and 4B and Fig. 5 show a charge transfer device according to the second embodiment of the invention. Fig. 4 shows the cross sectional structure of the charge transfer device, with an illustration how charges are transferred, and Fig. 5 shows the waveforms of a pulse signal train applied to transfer electrodes.

20 As shown in Fig. 4, formed on the final output side of a horizontal charge transfer path 37 are a final transfer electrode FE, an output gate OG, a floating diffusion FD region (charge detecting layer), a reset gate RS, and a reset drain RD. The reset gate RS is an electrode used when charges accumulated in the floating diffusion FD region are reset to an initial value. Reset charges are drained to the reset
25 drain RD.

The fundamental structure of the second embodiment is similar to that of the charge transfer device of the first embodiment. A different point of the charge transfer device of the second embodiment is that the final transfer electrode FE is formed adjacent to the final charge transfer stage of the horizontal charge transfer path.

Charges in the horizontal charge transfer path 37 are transferred toward the floating diffusion FD region by a six-phase drive method. A signal $\Phi 1L$ is applied to the final transfer electrode FE. Charges are stored in a well region (n-type semiconductor layer) under the final transfer electrode FE.

Fig. 5 shows the waveforms of pulse signals applied to charge transfer electrodes.

The pulse signals $\Phi 1$ to $\Phi 6$ are applied to charge transfer electrodes to transfer signal charges in the horizontal charge transfer path by a six-phase drive method.

As the pulse signal $\Phi 1L$ takes a high level, charges are stored in a well of a semiconductor region (n-type semiconductor layer) under the final transfer electrode FE, and as the pulse signal $\Phi 1L$ takes a low level, the stored charges are transferred to the floating diffusion FD region.

Fig. 4 also illustrates how charges are transferred at times t_1 to t_7 shown in Fig. 5.

At time t_1 , the drive pulse $\Phi 1L$ takes a high level voltage. The potential of the semiconductor region (n-type semiconductor layer) under the final transfer electrode FE lowers to form a potential well. The signal $\Phi 1$ takes the low level voltage, the signals $\Phi 2$ to $\Phi 5$ takes a high level voltage, and the signal $\Phi 6$ takes the low level voltage. Charges are stored in the semiconductor regions under the

horizontal charge transfer electrodes applied with the high level voltage. Since the signal Φ_6 takes the low level, a potential barrier is formed in the semiconductor region of the final charge transfer stage of the horizontal charge transfer path. The stored charges are not transferred to the semiconductor region under the final transfer electrode FE.

At time t_2 , the signal Φ_2 takes the low level and the signal Φ_6 takes the high level. The potential barrier formed in the semiconductor region of the final charge transfer stage of the horizontal charge transfer path disappears. The charges stored in the final charge transfer stage of the horizontal charge transfer path are therefore transferred to the semiconductor region under the final transfer electrode FE. The transferred charges are stored in the well formed in the semiconductor region.

At time t_3 , the signal Φ_3 takes the low level. Charges in the horizontal charge transfer path are transferred to the semiconductor region under the final transfer electrode FE. The transferred charges are stored in the well formed in the semiconductor region.

At time t_4 , the signal Φ_4 takes the low level. Charges in the horizontal charge transfer path are transferred to the semiconductor region under the final transfer electrode FE. The transferred charges are stored in the well formed in the semiconductor region.

At time t_5 , the signal Φ_5 takes the low level. Similar to the above, charges in the horizontal charge transfer path are transferred to the semiconductor region under the final transfer electrode FE and stored in the well.

At time t_6 , the signal Φ_6 takes the low level. Similar to the above, charges in the horizontal charge transfer path are transferred to the semiconductor region under the final transfer electrode FE and stored in the well.

At time t7, a high level voltage is applied to the output gate OG, and the signal $\Phi 1L$ takes the low level. The charges stored in the semiconductor region under the final transfer gate FE are transferred to the floating diffusion FD region because of a raised potential in this semiconductor region.

5 By repeating the above operations, as the time lapses (from t1 to t6), charges transferred in the horizontal charge transfer path are gradually stored in the well formed in the semiconductor region (n-type semiconductor layer) under the final transfer electrode FE. At time t7, the stored charges are transferred to the floating diffusion FD region at a time.

10 Although the horizontal charge transfer path 37 is driven by the six-phase drive method, charges are transferred to the charge detecting layer only when the sixth phase drive pulse is applied. Although the output signal waveform has a frequency different from that when charges in the horizontal charge transfer path 37 are transferred by the two-phase drive method, the data rate is equal.

15 With this method, a signal hold time in the floating diffusion FD region can be prolonged.

The charges temporarily stored in the semiconductor region under the final transfer electrode FE can be transferred to the floating diffusion FD region at a time. Signal detection, output timings and an output period can be set almost
20 arbitrarily, and an output suitable for signal processing can be obtained.

A noise reduction process such as a CDS process (process by a correlation double sampling circuit) can be executed.

Next, a charge transfer device according to the third embodiment of the invention will be described with reference to Fig. 6, Figs. 7, and Fig. 8. Fig. 6 is a plan
25 view of the charge transfer device, Fig. 7 shows the cross sectional structure of the

charge transfer device, with an 7B illustrations how charges are transferred, and Fig. 8 shows the waveforms of drive pulses.

As shown in Fig. 6 and Figs. 7, a charge transfer device B has: similar to the charge transfer device A described earlier, a semiconductor substrate 1; an n-type semiconductor layer 7 formed on the surface of the semiconductor substrate 1; charge transfer electrodes 21 of polysilicon formed on an interlayer insulating film 15 on the n-type semiconductor layer 7; and pulse signal generators 25 (25c, 25d) for applying pulse voltages to the charge transfer electrodes.

The charge transfer electrodes 21 include first charge transfer electrodes 21-1, 21-3, 21-5,... made of first layer polysilicon and second charge transfer electrodes 21-2, 21-4, 21-6,... made of second layer polysilicon. The first and second charge transfer electrodes are disposed alternately in the horizontal direction.

The regions of the n-type semiconductor layer 7 under the first charge transfer electrodes 21-1, 21-3, 21-5,... made of the first layer polysilicon have a low n-type impurity concentration, forming potential barriers (B). The regions of the n-type semiconductor layer 7 under the second charge transfer electrodes 21-2, 21-4, 21-6,... made of the second layer polysilicon have a high n-type impurity concentration, forming potential wells (W).

First and second two charge transfer electrodes 21 adjacent to each other in the horizontal direction, e.g., the first and second charge transfer electrodes 21-1 and 21-2, or 21-3 and 21-4, are connected in common. A pulse signal $\Phi 2$ is applied from the pulse signal generator 25 (25c) to the commonly connected charge transfer electrodes 21-1 and 21-2. A pulse signal $\Phi 1$ is applied from the pulse signal generator 25 (25c) to the commonly connected charge transfer electrodes 21-3 and 21-4. The pulse signal $\Phi 2$ is applied from the pulse signal generator 25 (25c) to the

commonly connected charge transfer electrodes 21-5 and 21-6.

Similarly, pairs of two adjacent charge transfer electrodes disposed alternately in the horizontal direction are alternately applied with pulse signals Φ_2 , Φ_1 , Φ_2 , Φ_1 ,... from the pulse signal generator 25 (25c).

5 The pulse signal generator 25 (25d) independently applies pulse signals Φ_1 to Φ_6 to the transfer electrodes 21-1 to 21-6.

If the two-phase pulse signals Φ_1 and Φ_2 are alternately applied to every transfer electrode pair 21 of the charge transfer device B, it operates as a two-phase drive type CCD.

10 If the six-phase pulse signals Φ_1 to Φ_6 are alternately applied to every transfer electrode pair 21 of the charge transfer device B, it operates as a six-phase drive type CCD.

15 The length of the charge transfer stage used by the six-phase drive method is three times that by the two-phase drive method. The length of the charge transfer stage used by the k-phase drive method (k is a positive integer) is k/2 times that by the two-phase drive method.

Fig. 8 shows the waveforms of six-phase pulse signals generated by the pulse signal generator 25 (25d).

20 The drive pulses Φ_1 to Φ_6 rise from the low level to the high level and fall from the high level to the low level, in the sequential order of Φ_1 to Φ_6 , as seen along the abscissa (time) in Fig. 8. The period while the pulse signals take the high level is generally equal.

25 Fig. 7 also shows the charge distribution in the charge transfer device B at times t_1 , t_2 and t_3 shown in Fig. 8. Charge signals transferred from the vertical charge transfer paths are transferred in the horizontal direction sequentially from time

t1 to time t3. As compared to a conventional two-phase charge transfer, a ratio of empty charge transfer stages to total stages is low. The charge transfer efficiency is therefore improved.

If both the n-phase drive and (n x m)-phase drive methods are to be used, the electric capacity of the second well (semiconductor region under the last transfer electrode FE) is set (n x m - 3) times or more that of the first well (well region in the horizontal charge transfer path).

For example, during the time between time t1 and t2, there are three electrodes applied with the low level among the six electrodes. This state can be said that a phase margin of pulse signals is large. Since the three electrodes take the low level, charges are not stored in three wells.

From this reason, a value of (n x m - 3) times is appropriate.

A solid state image pickup device according to the fourth embodiment of the invention will be described with reference to Figs. 9 and 10.

As shown in Fig. 9, a solid state image pickup device C according to the fourth embodiment of the invention has: a semiconductor substrate 31; photoelectric conversion elements 33 regularly disposed on the semiconductor substrate 31; vertical charge transfer paths 35 extending in the vertical direction and formed for each set of photoelectric conversion elements 33 regularly disposed in a column direction (vertical direction); a channel stopper 41 extending in the vertical direction and partitioning the vertical charge transfer paths 35 along the horizontal direction; and a horizontal charge transfer path 37 extending in the horizontal direction and connected to one ends of the vertical charge transfer paths 35 in the vertical direction.

The solid type image pickup device C also has: a plurality of vertical charge transfer electrodes EV (EV1, EV2,..., EV12) extending in the horizontal

direction, two electrodes being provided for each row of photoelectric conversion elements 33; horizontal charge transfer electrodes EH (EH1, EH2, EH3,...) made of first layer polysilicon and second layer polysilicon and formed alternately on the horizontal charge transfer path 37 in the horizontal direction; and read gates 33a each
5 formed between the photoelectric conversion element 33 and vertical charge transfer path 35 for reading charges accumulated in the photoelectric conversion element 33 to the vertical charge transfer path 35.

The solid state image pickup device C has also pulse signal generators 25 (25a, 25b, 25c) for generating pulse signals and applying them to the vertical and
10 horizontal charge transfer electrodes EV and EH.

Two adjacent horizontal charge transfer electrodes EH in the horizontal direction, e.g., the electrodes EH1 and EH2, and EH3 and EH4, are connected in common.

Of the pulse generators 25, the pulse generators 25a and 25b are used
15 for applying pulse signals to the horizontal charge transfer electrodes, whereas the pulse generator 25c is used for applying pulse signals to the vertical charge transfer paths.

The photoelectric conversion elements 33 include green (G) photoelectric conversion elements 33a, red (R) photoelectric conversion elements 33b
20 and blue (B) photoelectric conversion elements 33c.

A plurality of G photoelectric conversion elements regularly disposed in the vertical direction is disposed every second columns.

In a column adjacent in the horizontal direction to the column of G photoelectric conversion elements disposed in the vertical direction, B and R
25 photoelectric conversion elements are alternately disposed shifted by a half pitch of G

photoelectric conversion elements. The solid state image pickup device has a so-called pixel-shift layout.

In a row adjacent in the vertical direction to the row of G photoelectric conversion element disposed in the horizontal direction, B and R photoelectric conversion elements are alternately disposed in the horizontal direction.

Fig. 9 illustrates a transfer state of signal charges when they are read from all pixels of the solid state image pickup device having the pixel-shift layout. In this transfer state, charge signals disposed in one row in the order of R, G, R, G,... are transferred in parallel in the vertical charge transfer paths 35.

If charge signals transferred from photoelectric conversion elements of k columns adjacent in the horizontal direction to the horizontal charge transfer path are to be added and read, the charge signals in the horizontal charge transfer path are driven by a 2k-phase drive method.

After charge signals are transferred to the horizontal charge transfer path 37, six-phase drive pulses are applied from the pulse signal generator 25 (25b) to the horizontal charge transfer electrodes EH. In this case, an addition signal of $R + G + B$, an addition signal of $2G + R$ and an addition signal of $2G + B$ are output at a half of the data rate of the two-phase drive method. These output signals are processed by a signal processing circuit to display a monitor image.

If two-phase signal pulses are applied to the horizontal charge transfer electrodes EH, charges can be read from all pixels similar to the normal operation of a solid state image pickup device.

Fig. 10 illustrates a control method for a solid state image pickup device according to a modification of the fourth embodiment.

The solid state image pickup device shown in Fig. 10 has the structure

similar to that shown in Fig. 9.

When signal charges in the photoelectric conversion element 33 are read to the vertical charge transfer path 35, for example, a pulse signal Φ_{v2} takes a high positive voltage, e.g., 15 V. Signal charges in the B and R photoelectric conversion elements 33 are read to the vertical charge transfer paths 35.

Signal charges in the vertical charge transfer paths 35 are transferred by a four-phase drive method toward the horizontal charge transfer path by applying pulse signals Φ_{v1} to Φ_{v4} to the vertical charge transfer electrodes.

In this modification, the positions of read gates 40 are different between the same color photoelectric conversion elements.

For example, when the read pulse signal Φ_{v2} is applied, signal charges are read only from specific R and B photoelectric conversion elements in the same row. In this example, the read gates 40 are positioned either on the EV1 or EV2 electrode side corresponding to the pulse signals Φ_{v1} and Φ_{v2} . Similarly, in other rows, the positions of read gates 40 are different between the same color photoelectric conversion elements. In this manner, a thinning operation in the horizontal direction is possible. In this example shown in Fig. 10, signal charges can be read from the photoelectric conversion elements of one column per three columns by applying the read pulses to the charge transfer electrodes.

If the number of vertical charge transfer electrodes per one row of photoelectric conversion elements is increased, the number n of the $1/n$ horizontal thinning can be changed flexibly.

For example, if the number of vertical charge transfer electrodes per one row is increased to four and the position of each read gate for each of photoelectric conversion elements on the same row is set to one of the four positions corresponding

to the four vertical charge transfer electrodes, then the number n of the $1/n$ horizontal thinning can be changed depending upon to which vertical charge transfer electrode or electrodes the read pulse is applied.

Further, if control gates are provided between the vertical charge transfer paths and horizontal charge transfer path, the number n of the $1/n$ horizontal thinning can be changed flexibly. Specifically, the control gates select desired vertical charge transfer paths and signal charges are read only from the selected vertical charge transfer paths. This method is disclosed in US Patent Application filed on June 7, 2000, the Case Docket No. P107317-00006. The contents of US Patent Application filed on June 7 are incorporated herein by reference and are construed as forming part of this specification.

With the control method for the solid image pickup device shown in Fig. 10, by applying read pulses to predetermined charge transfer electrodes, charges can be read from photoelectric conversion elements 33 of one row per four rows ($1/4$ vertical thinning read operation). Signal charges in the vertical charge transfer paths 35 in one column per three columns can be transferred to the horizontal charge transfer path 37 ($1/3$ horizontal thinning read operation).

The $1/k$ horizontal thinning is executed by selectively reading signal charges from photoelectric conversion elements of one column per four columns adjacent in the horizontal direction, and then signal charges in the horizontal charge transfer path are driven by the $2k$ -phase drive method.

As the six-phase pulse signals $\Phi 1$ to $\Phi 6$ are applied, the horizontal charge transfer path 37 is driven by the six-phase drive method. As the six-phase drive method is used, signal charges transferred from vertical charge transfer paths of one column per three columns can be transferred in the horizontal charge transfer

path without an empty signal charge transfer.

With the above operation, signal charges thinned by 1/3 in the horizontal direction can be output. In this example shown in Fig. 10, thinned signal charges are output in the order of R, G, B, G,.... This solid state image pickup device can be used effectively for displaying a clear moving monitor image on a digital still camera.

Since signal charges in the horizontal charge transfer path are driven by the six-phase drive method, the data rate lowers and the frequency of drive pulses lowers by 1/3. The consumption power is also reduced by 1/3.

A solid state image pickup device according to the fifth embodiment of the invention will be described with reference to Figs. 11 to 14.

In the structure of the solid state image pickup device shown in Fig. 11 and 13, pulse signals $\Phi 1$ to $\Phi 4$ are applied to pairs of two horizontal charge transfer electrodes EH.

Fig. 11 illustrates an operation of reading all pixels.

Photoelectric conversion elements 33 have an RGB vertical stripe color filter layout regularly disposing R, G and B photoelectric conversion elements in a vertical direction.

Fig. 12 shows the waveforms of drive pulses used for two-phase driving the horizontal charge transfer path 37. The drive pulses $\Phi 1$ and $\Phi 3$ have the same waveform, and the drive pulses $\Phi 2$ and $\Phi 4$ have the same waveform. Similar to a charge transfer in a horizontal charge transfer path by the two-phase drive method, signal charges can be read from all photoelectric conversion elements.

The solid state image pickup device shown in Fig. 13 has the same structure as that shown in Fig. 11. Fig. 13 shows the distribution of image signals when a 1/2 vertical and horizontal thinning read operations are executed. Also by the

1/2 horizontal thinning read method, an RGB stripe signal is output.

Fig. 14 shows the waveforms of drive pulses applied to the horizontal charge transfer electrodes EH for the 1/2 vertical and horizontal thinning read operations.

5 The pulse signals $\Phi 1$ to $\Phi 4$ rise from the low level to the high level in the sequential order of $\Phi 1$ to $\Phi 4$ and fall from the high level to the low level in this order.

By applying the four-phase drive pulses to the horizontal charge transfer electrodes EH, the 1/2 horizontal thinning operation can be executed without an empty charge transfer. The consumption power is reduced by 1/2.

10 The shape of a pixel may be a square, a polygon or the like in addition to the regular hexagon.

The present invention has been described in connection with the preferred embodiments. The invention is not limited only to the above embodiments. It is apparent that various modifications, improvements, combinations, and the like can
15 be made by those skilled in the art.

WHAT IS CLAIMED IS:

1. A charge transfer device comprising:

a semiconductor substrate;

a charge transfer path formed in said semiconductor substrate and

5 made of a first conductivity type semiconductor layer;

a plurality of charge transfer electrodes formed near above said charge transfer path; and

a first pulse signal generator circuit for applying either a first pulse signal train for n-phase (n being an integer larger than 1) driving of charges in said charge transfer path to said charge transfer electrodes or a second pulse signal train for (n + 1)-phase driving of charges in said charge transfer path to said charge transfer electrodes.

2. A charge transfer device comprising:

a semiconductor substrate;

a charge transfer path formed in said semiconductor substrate and made of a first conductivity type semiconductor layer;

a plurality of charge transfer electrodes formed near above said charge transfer path; and

a second pulse signal generator circuit for applying either a first pulse signal train for n-phase driving (n being an integer larger than 1) of charges in said charge transfer path to said charge transfer electrodes or a third pulse signal train for (n x m)-phase driving (m being an integer larger than 1) of charges in said charge transfer path to said charge transfer electrodes.

3. A charge transfer device comprising:

a semiconductor substrate;

a charge transfer path formed in said semiconductor substrate and made of a first conductivity type semiconductor layer, said charge transfer path having

5 first barrier layers having a high potential and second well layers having a low potential, disposed alternately;

a plurality of first and second charge transfer electrodes alternately formed near above the first barrier layers and first well layers of said charge transfer path;

10 a plurality of charge transfer electrode pairs each having adjacent first and second two charge transfer electrodes connected together; and

a third pulse signal generator circuit for applying either a fourth pulse signal train of two-phase for 2-phase driving of charges in said charge transfer path to two charge transfer electrode pairs or a fifth pulse signal train for 2k-phase driving or
15 more of charges in said charge transfer path to the charge transfer electrode pairs.

4. A charge transfer device according to claim 3, further comprising:

a charge storage region formed adjacent to a final stage of the charge transfer electrodes for temporarily storing charges transferred in said charge transfer
20 path; and

a charge detecting region for detecting an amount of charges stored in said charge storage region.

5. A charge transfer device according to claim 4, wherein said charge storage region
25 comprises:

a second barrier layer and a second well layer formed adjacent to each other in said charge transfer path;

a third charge transfer electrode and a fourth charge transfer electrode formed above the second barrier layer and the second well layer; and

5 a stored charge output pulse generator circuit connected to said third charge transfer electrode and said fourth charge transfer electrode, for generating a stored charge output pulse.

6. A charge transfer device according to claim 3, wherein the second well layer has
10 an electric capacity larger than an electric capacity of the first well layer and the channel transfer device further comprises a floating diffusion region formed adjacent to the second well layer for detecting an amount of charges transferred from said charge transfer path.

15 7. A charge transfer device comprising:

a semiconductor substrate;

a charge transfer path formed in said semiconductor substrate and made of a first conductivity type semiconductor layer;

a plurality of charge transfer electrodes formed near above said charge
20 transfer path; and

a first pulse signal generator circuit for applying either a first pulse signal train for n-phase (n being an integer larger than 1) driving of charges in said charge transfer path to said charge transfer electrodes or a second pulse signal train for (n + 1)-phase driving of charges in said charge transfer path to said charge transfer
25 electrodes;

a charge storage region formed adjacent to a final stage of the charge transfer electrodes for temporarily storing charges transferred in said charge transfer path; and

5 a charge detecting region for detecting an amount of charges stored in said charge storage region.

8. A charge transfer device comprising:

a semiconductor substrate;

10 a charge transfer path formed in said semiconductor substrate and made of a first conductivity type semiconductor layer;

a plurality of charge transfer electrodes formed near above said charge transfer path; and

15 a second pulse signal generator circuit for applying either a first pulse signal train for n-phase driving (n being an integer larger than 1) of charges in said charge transfer path to said charge transfer electrodes or a third pulse signal train for (n x m)-phase driving (m being an integer larger than 1) of charges in said charge transfer path to said charge transfer electrodes;

20 a charge storage region formed adjacent to a final stage of the charge transfer electrodes for temporarily storing charges transferred in said charge transfer path; and

a charge detecting region for detecting an amount of charges stored in said charge storage region.

25 9. A charge transfer device comprising:

a semiconductor substrate;

a charge transfer path formed in said semiconductor substrate and made of a first conductivity type semiconductor layer, said charge transfer path having first barrier layers and second well layers alternately disposed adjacent to each other;

5 a plurality of charge transfer electrodes formed adjacent to each other above said charge transfer path;

a second pulse signal generator circuit for applying either a first pulse signal train for n-phase driving (n being an integer larger than 1) of charges in said charge transfer path to said charge transfer electrodes or a third pulse signal train for
10 (n x m)-phase driving (m being an integer larger than 1) of charges in said charge transfer path to said charge transfer electrodes;

a charge storage region formed adjacent to a final stage of the charge transfer electrodes for temporarily storing charges transferred in said charge transfer path; and

15 a charge detecting region for detecting an amount of charges stored in said charge storage region,

wherein said charge storage region comprises:

a second barrier layer and a second well layer formed adjacent to each other in said charge transfer path;

20 a third charge transfer electrode and a fourth charge transfer electrode formed above the second barrier layer and the second well layer; and

a stored charge output pulse generator circuit connected to said third charge transfer electrode and said fourth charge transfer electrode, for generating a stored charge output pulse, and

25 wherein an electric capacity of the second well layer has an electric

capacity by $(n \times m^{-3})$ times or more larger than an electric capacity of the first well.

10. A solid state image pickup device comprising; a semiconductor substrate; a plurality of photoelectric conversion elements regularly disposed in row and column directions on the semiconductor substrate; a plurality of vertical charge transfer paths extending in a vertical direction and each disposed adjacent to each of a plurality of photoelectric conversion element columns regularly disposed in the column direction; a read gate formed between each photoelectric conversion element and a corresponding vertical charge transfer path for transferring charges accumulated in the photoelectric conversion element to the vertical charge transfer path; a horizontal charge transfer path formed at one ends of the plurality of vertical charge transfer paths for transferring charges in a horizontal direction; and an output amplifier for amplifying charges transferred by the horizontal charge transfer path and outputting the amplified charges, the horizontal charge transfer path including: a charge transfer path formed in the semiconductor substrate and made of a first conductivity type semiconductor layer, the charge transfer path having first barrier layers having a high potential and second well layers having a low potential, disposed alternately; a plurality of first and second charge transfer electrodes alternately formed near above the first barrier layers and first well layers of the charge transfer path; a plurality of charge transfer electrode pairs each having adjacent first and second two charge transfer electrodes connected together; and a third pulse signal generator circuit for applying either a fourth pulse signal train of two-phase for 2-phase driving of charges in said charge transfer path to two charge transfer electrode pairs or a fifth pulse⁻ signal train for 2k-phase driving or more of charges in the charge transfer path to the charge transfer electrode pairs.

11. A solid state image pickup device comprising; a semiconductor substrate; a plurality of photoelectric conversion elements regularly disposed in row and column directions on the semiconductor substrate; a plurality of vertical charge transfer paths extending in a vertical direction and each disposed adjacent to each of a plurality of photoelectric conversion element columns regularly disposed in the column direction; a read gate formed between each photoelectric conversion element and a corresponding vertical charge transfer path for transferring charges accumulated in the photoelectric conversion element to the vertical charge transfer path; a horizontal charge transfer path formed at one ends of the plurality of vertical charge transfer paths for storing charges in first well layers and transferring stored charges in a horizontal direction; and an output amplifier for amplifying charges transferred by the horizontal charge transfer path and outputting the amplified charges, the horizontal charge transfer path including: a first conductivity type semiconductor layer formed in the semiconductor substrate; a plurality of charge transfer electrodes formed adjacent to each other above the horizontal charge transfer path; a second pulse signal generator circuit for applying either a fourth first signal train for n-phase driving (n being an integer larger than 1) of charges in said horizontal charge transfer path to the charge transfer electrodes or a third pulse signal train for (n x m)-phase driving or more (m being an integer larger than 1) of charges in the horizontal charge transfer path to the charge transfer electrodes; a charge storage region formed adjacent to a final stage of the charge transfer electrodes for temporarily storing charges transferred in the horizontal charge transfer path; and a charge detecting region for detecting an amount of charges stored in the charge storage region, the charge storage region including: a second barrier layer and a second well layer formed adjacent to each

other in said charge transfer path; a third charge transfer electrode and a fourth charge transfer electrode formed above the second barrier layer and the second well layer; and a stored charge output pulse generator circuit connected to the third and fourth charge transfer electrodes, for generating a stored charge output pulse, wherein

5 the second well layer has an electric capacity by $(n \times m - 3)$ times or more than an electric capacity of the first well layer.

12. A method of reading a solid state image pickup device, the solid state image pickup device including: a semiconductor substrate; a plurality of photoelectric

10 conversion elements regularly disposed in row and column directions on the semiconductor substrate; a plurality of vertical charge transfer paths extending in a vertical direction and each disposed adjacent to each of a plurality of photoelectric conversion element columns regularly disposed in the column direction; a read gate formed between each photoelectric conversion element and a corresponding vertical

15 charge transfer path for transferring charges accumulated in the photoelectric conversion element to the vertical charge transfer path; a horizontal charge transfer path formed at one ends of the plurality of vertical charge transfer paths for transferring charges in a horizontal direction; and an output amplifier for amplifying charges transferred by the horizontal charge transfer path and outputting the amplified

20 charges, the horizontal charge transfer path including: a charge transfer path formed in the semiconductor substrate and made of a first conductivity type semiconductor layer, the charge transfer path having first barrier layers having a high potential and second well layers having a low potential, disposed alternately; a plurality of first and second charge transfer electrodes alternately formed near above the first barrier

25 layers and first well layers of the charge transfer path; a plurality of charge transfer

electrode pairs each having adjacent first and second two charge transfer electrodes connected together; and a third pulse signal generator circuit for applying either a fourth pulse signal train of two-phase for 2-phase driving of charges in said charge transfer path to two charge transfer electrode pairs or a fifth pulse signal train for 2k-
5 phase driving or more of charges in the charge transfer path to the charge transfer electrode pairs, the method comprising:

either a step of, when charges accumulated in all photoelectric conversion elements are read, transferring charges in the horizontal charge transfer path by a two-phase drive method; or

10 a step of executing a $1/k$ horizontal thinning operation by selectively reading charges from photoelectric conversion elements adjacent in the horizontal direction of one column per k columns and transferring charges in the horizontal charge transfer path by a $2k$ -phase drive method.

15 13. A method of reading a solid state image pickup device, the solid state image pickup device including: a semiconductor substrate; a plurality of photoelectric conversion elements regularly disposed in row and column directions on the semiconductor substrate; a plurality of vertical charge transfer paths extending in a vertical direction and each disposed adjacent to each of a plurality of photoelectric
20 conversion element columns regularly disposed in the column direction; a read gate formed between each photoelectric conversion element and a corresponding vertical charge transfer path for transferring charges accumulated in the photoelectric conversion element to the vertical charge transfer path; a horizontal charge transfer path formed at one ends of the plurality of vertical charge transfer paths for
25 transferring charges in a horizontal direction; and an output amplifier for amplifying

charges transferred by the horizontal charge transfer path and outputting the amplified charges, the horizontal charge transfer path including: a charge transfer path formed in the semiconductor substrate and made of a first conductivity type semiconductor layer, the charge transfer path having first barrier layers having a high potential and second well layers having a low potential, disposed alternately; a plurality of first and second charge transfer electrodes alternately formed near above the first barrier layers and first well layers of the charge transfer path; a plurality of charge transfer electrode pairs each having adjacent first and second two charge transfer electrodes connected together; and a third pulse signal generator circuit for applying either a fourth pulse signal train of two-phase for 2-phase driving of charges in said charge transfer path to two charge transfer electrode pairs or a fifth pulse signal train for 2k-phase driving or more of charges in the charge transfer path to the charge transfer electrode pairs, the method comprising:

either a step of, when charges accumulated in all photoelectric conversion elements are read, transferring charges in the horizontal charge transfer path by a two-phase drive method; or

a step of 2k-phase driving the horizontal charge transfer path when charges of j columns of photoelectric conversion elements are transferred in the horizontal charge transfer path and read through addition.

14. A method of reading a solid state image pickup device, the solid state image pickup device including: a semiconductor substrate; a plurality of photoelectric conversion elements regularly disposed in row and column directions on the semiconductor substrate; a plurality of vertical charge transfer paths extending in a vertical direction and each disposed adjacent to each of a plurality of photoelectric

conversion element columns regularly disposed in the column direction; a read gate formed between each photoelectric conversion element and a corresponding vertical charge transfer path for transferring charges accumulated in the photoelectric conversion element to the vertical charge transfer path; a horizontal charge transfer path formed at one ends of the plurality of vertical charge transfer paths for storing charges in first well layers and transferring stored charges in a horizontal direction; and an output amplifier for amplifying charges transferred by the horizontal charge transfer path and outputting the amplified charges, the horizontal charge transfer path including: a first conductivity type semiconductor layer formed in the semiconductor substrate; a plurality of charge transfer electrodes formed adjacent to each other above the horizontal charge transfer path; a second pulse signal generator circuit for applying either a fourth first signal train for n-phase driving (n being an integer larger than 1) of charges in said horizontal charge transfer path to the charge transfer electrodes or a third pulse signal train for (n x m)-phase driving or more (m being an integer larger than 1) of charges in the horizontal charge transfer path to the charge transfer electrodes; a charge storage region formed adjacent to a final stage of the charge transfer electrodes for temporarily storing charges transferred in the horizontal charge transfer path; and a charge detecting region for detecting an amount of charges stored in the charge storage region, the charge storage region including: a second barrier layer and a second well layer formed adjacent to each other in said charge transfer path; a third charge transfer electrode and a fourth charge transfer electrode formed above the second barrier layer and the second well layer; and a stored charge output pulse generator circuit connected to the third and fourth charge transfer electrodes, for generating a stored charge output pulse, wherein the second well layer has an electric capacity by (n x m - 3) times or more than an electric

capacity of the first well layer, the method comprising:

a step of transferring charges from the charge storage region to the charge detecting region when charges are stored in the charge storage region $(n \times m - 3)$ times or more than an electric capacity of the first well.

5

ABSTRACT OF THE DISCLOSURE

A charge transfer device having: a semiconductor substrate; a charge transfer path formed in the semiconductor substrate and made of a first conductivity type semiconductor layer; a plurality of charge transfer electrodes formed near above the charge transfer path; and a first pulse signal generator circuit for applying either a first pulse signal train for n -phase (n being an integer larger than 1) driving of charges in the charge transfer path to the charge transfer electrodes or a second pulse signal train for $(n + 1)$ -phase driving of charges in the charge transfer path to the charge transfer electrodes.

10

FIG. 2

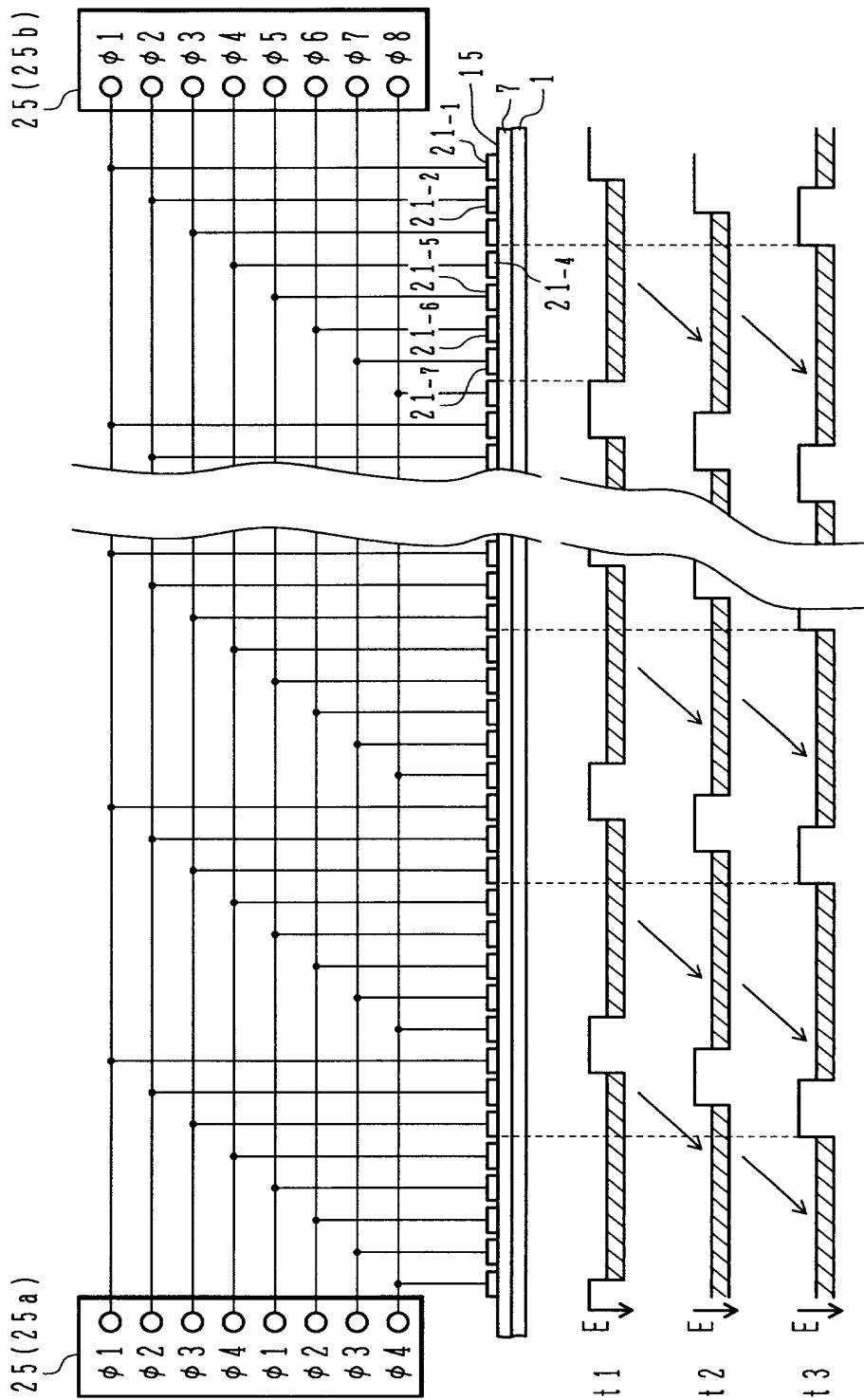


FIG.3

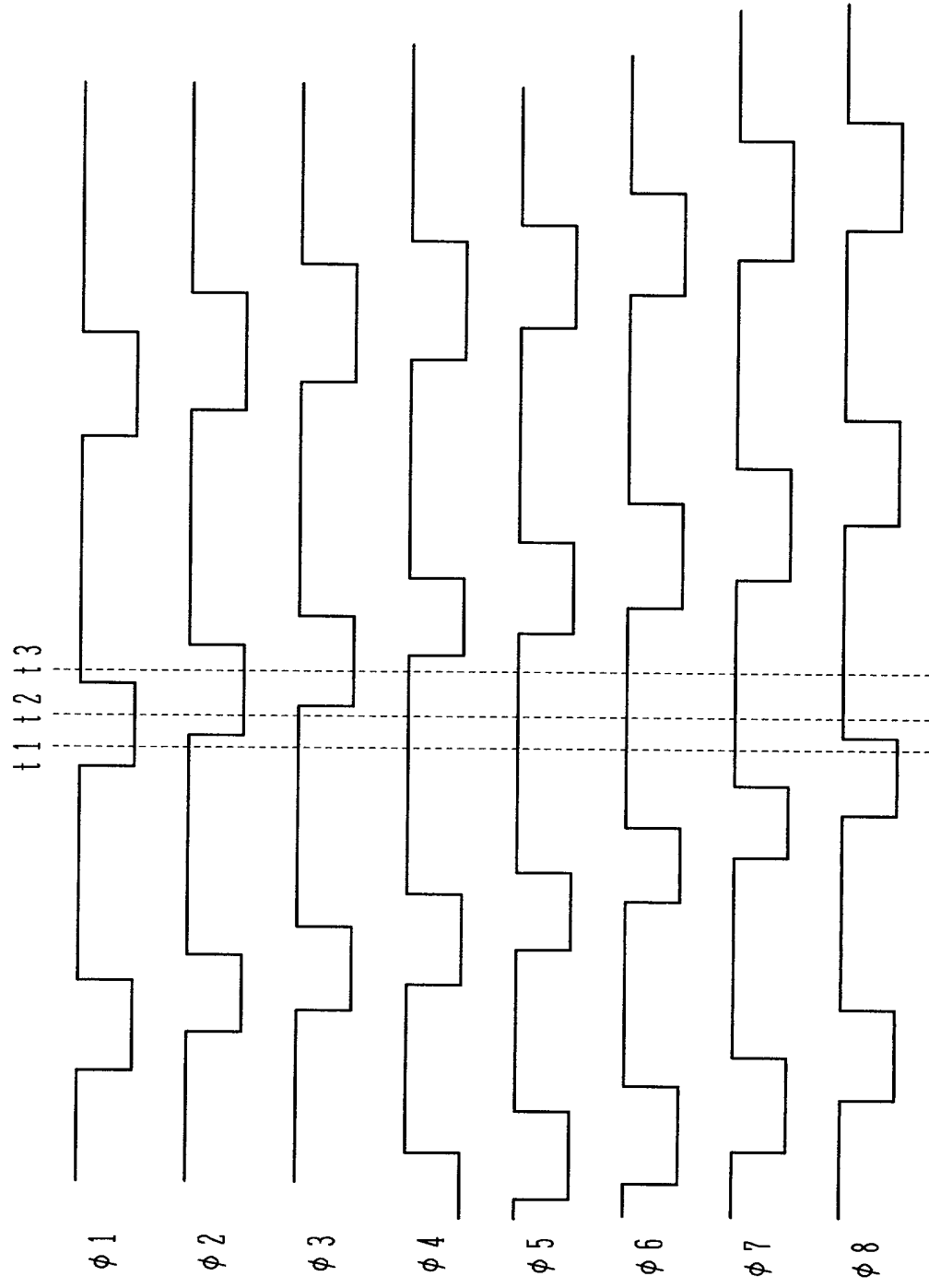


FIG. 4

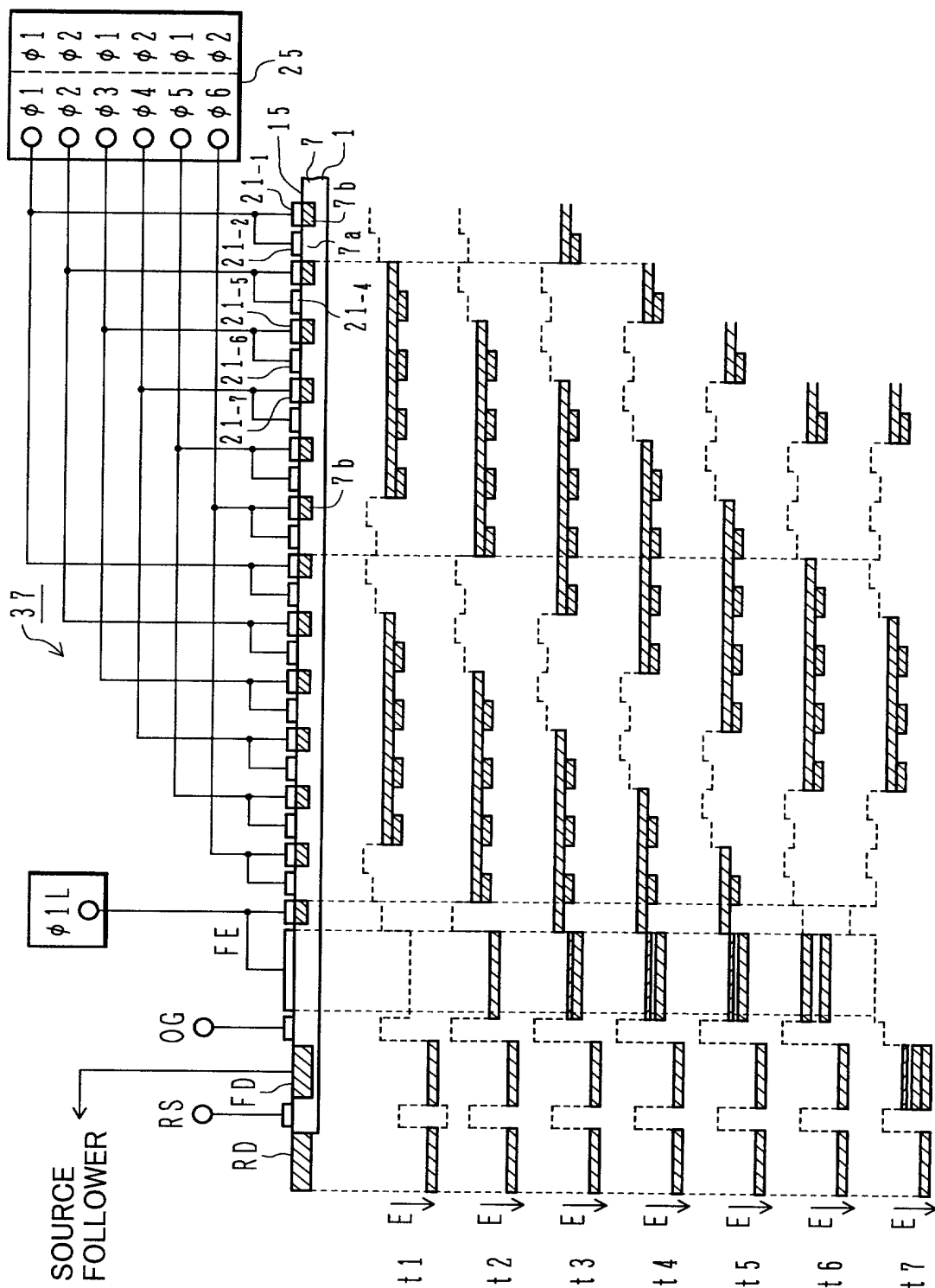


FIG. 5

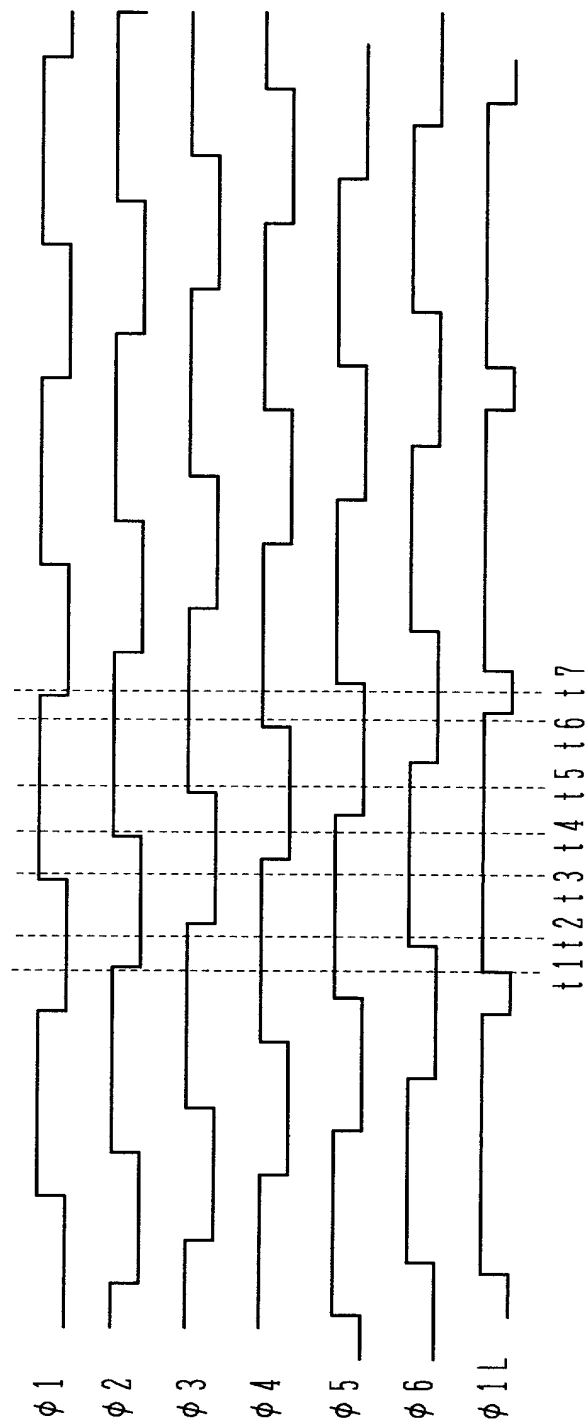


FIG. 6

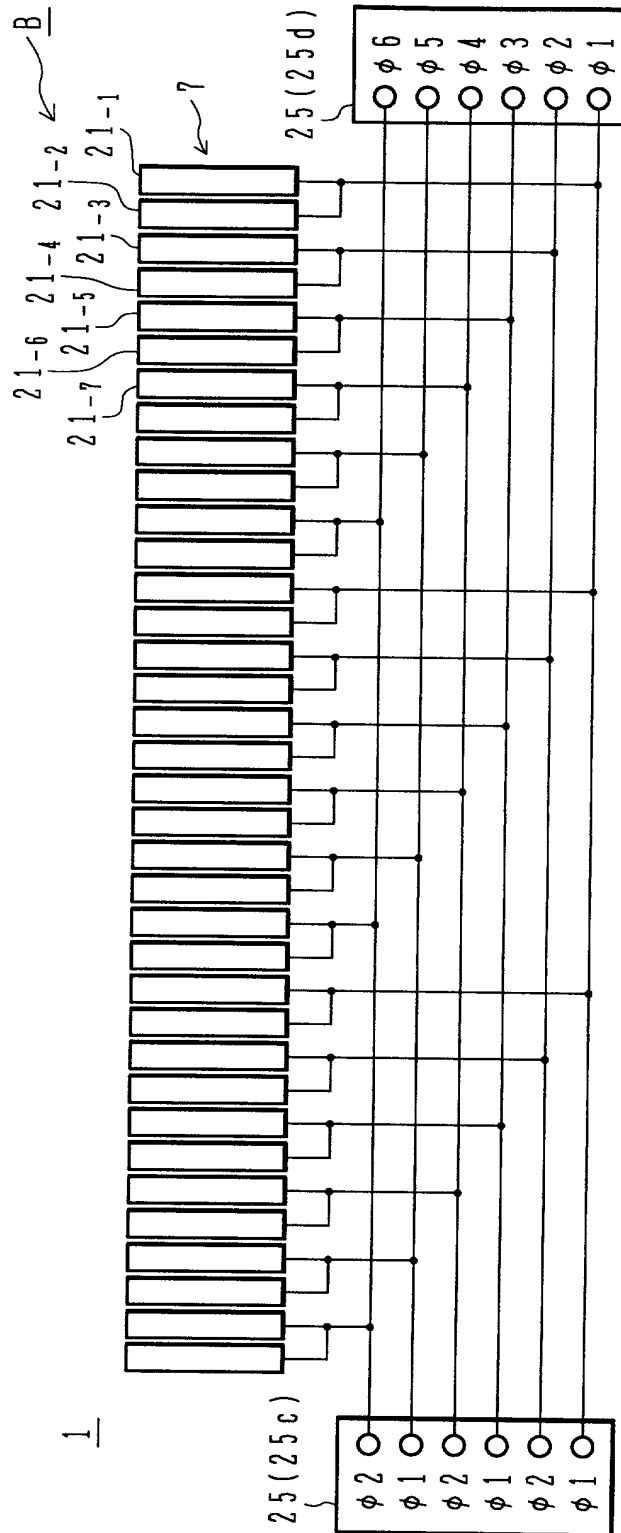


FIG.7

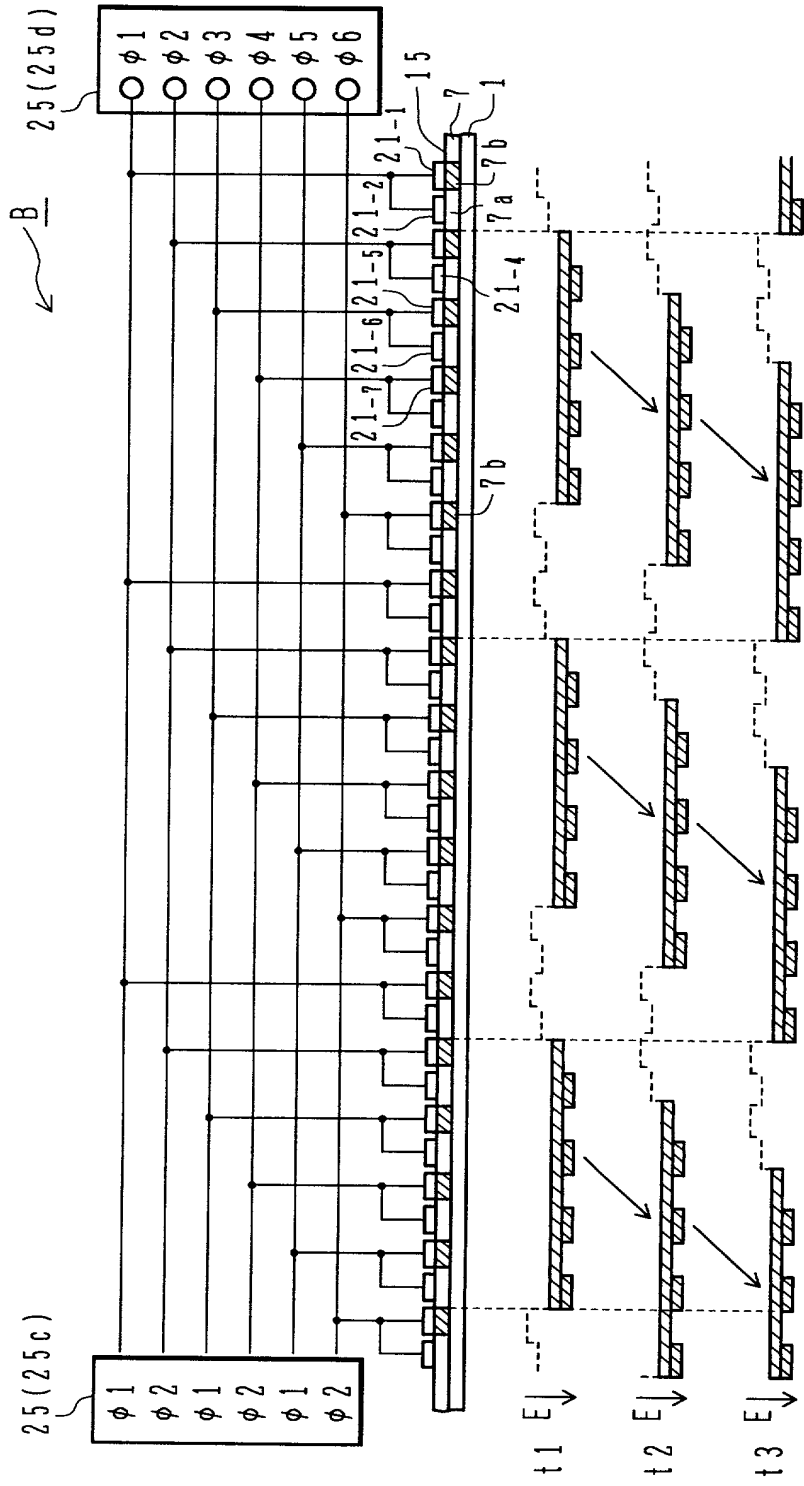


FIG. 8

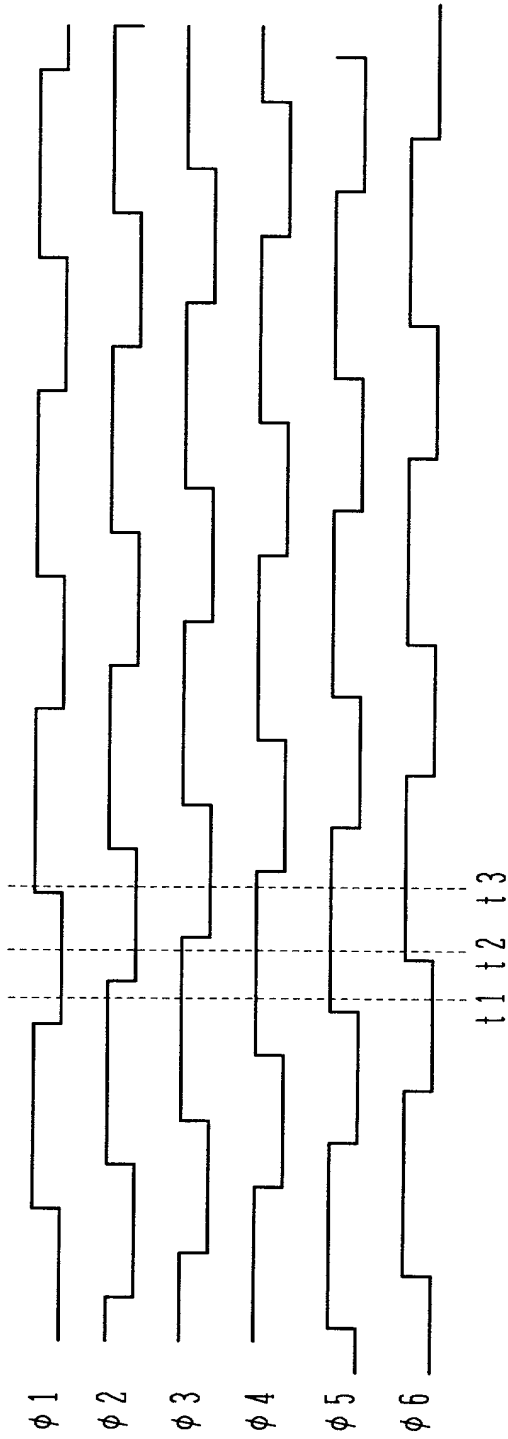


FIG. 9

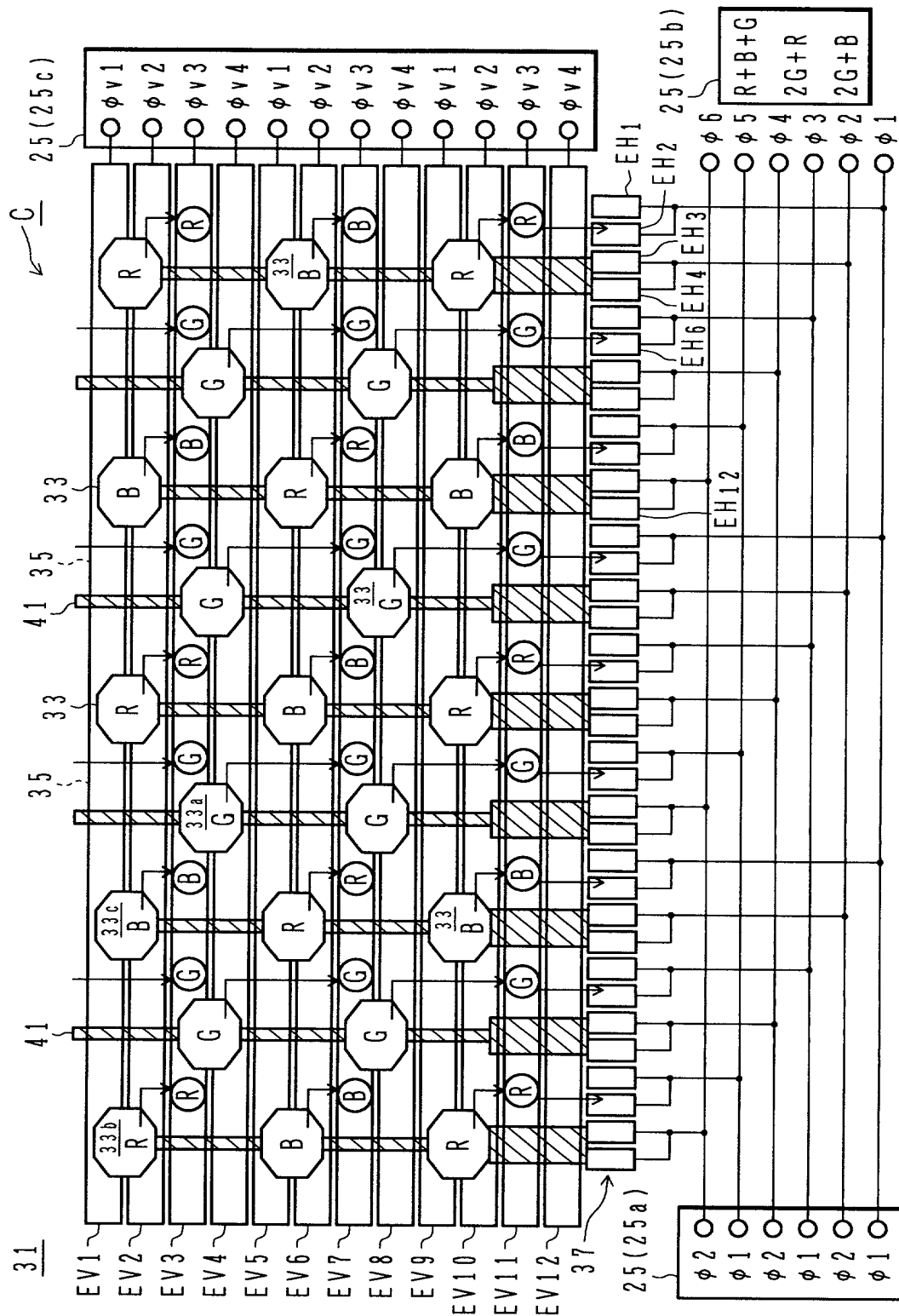


FIG.10

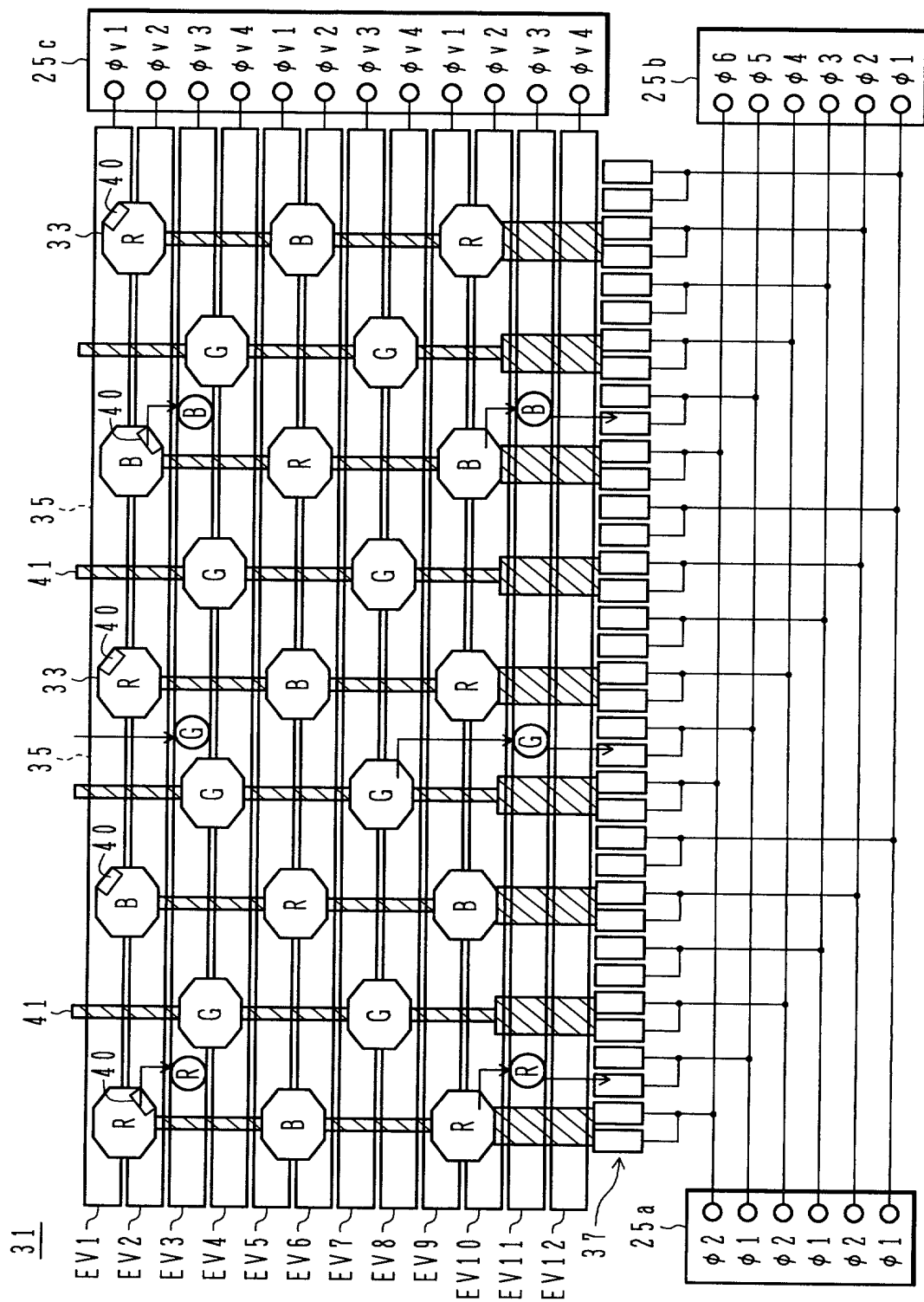


FIG.12

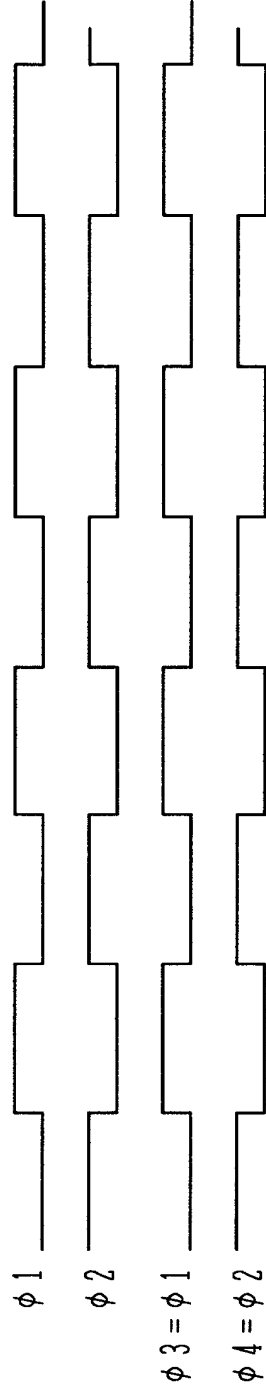


FIG. 13

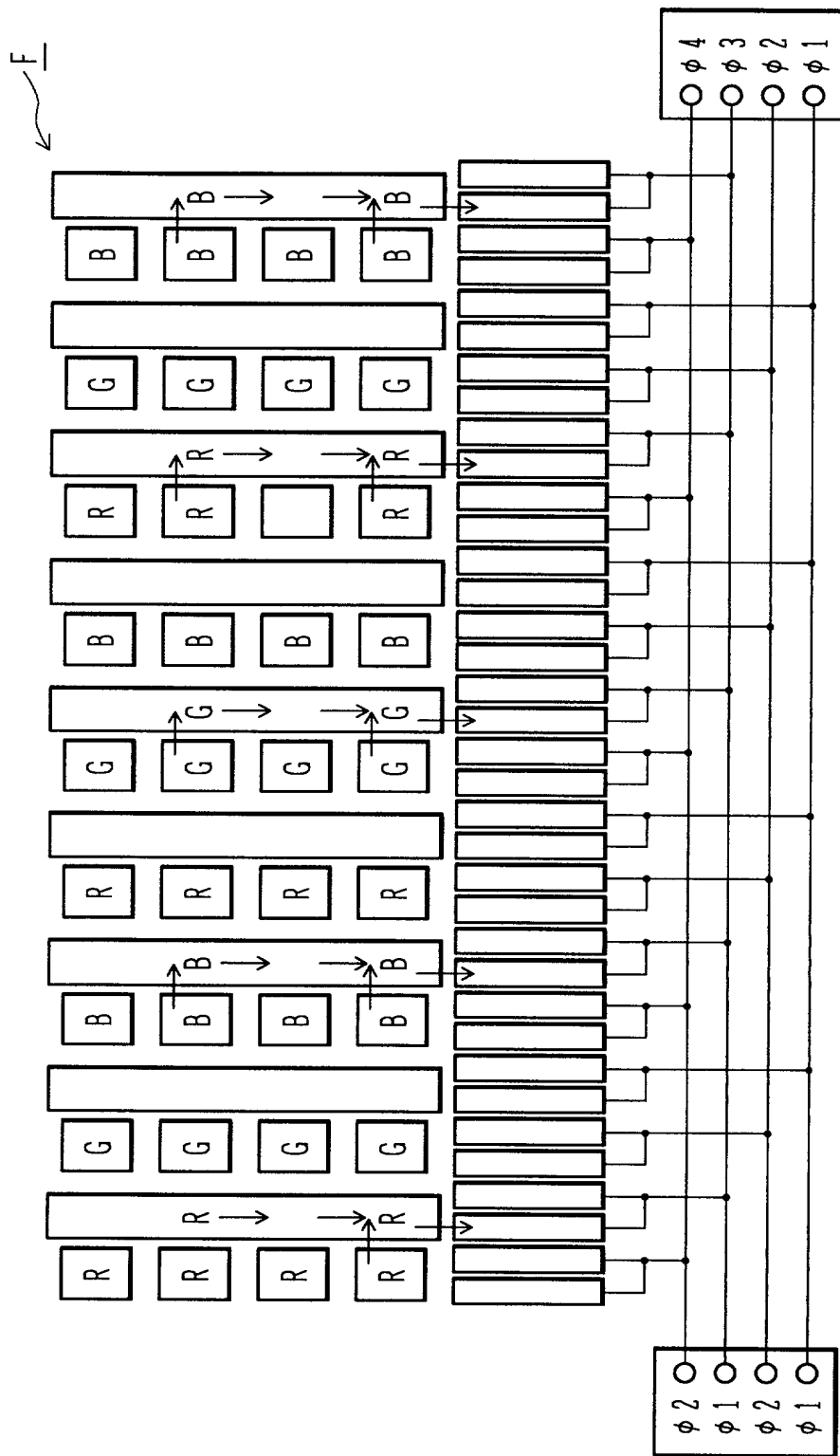


FIG.14

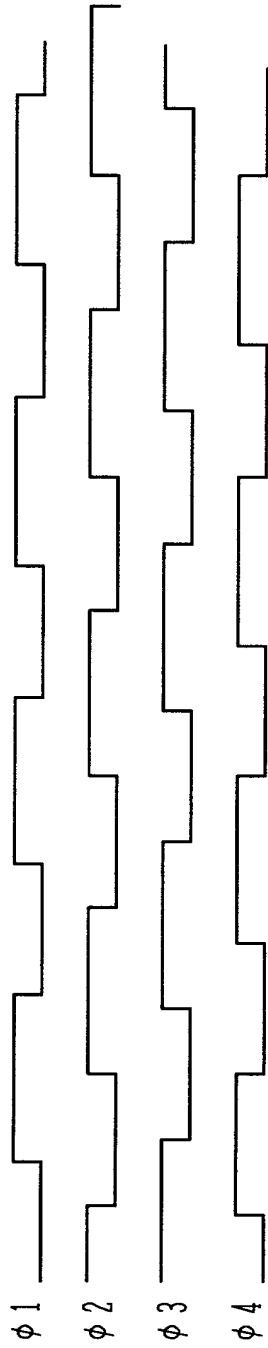


FIG.15A
(PRIOR ART)

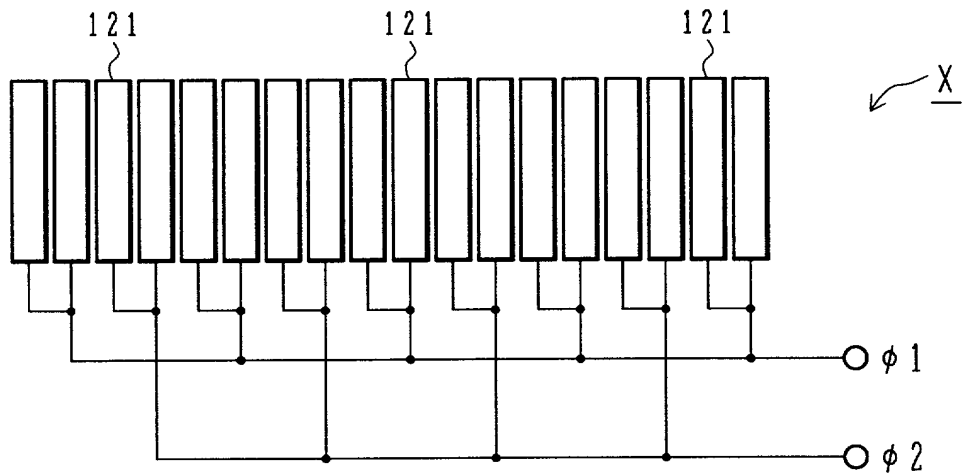


FIG.15B
(PRIOR ART)

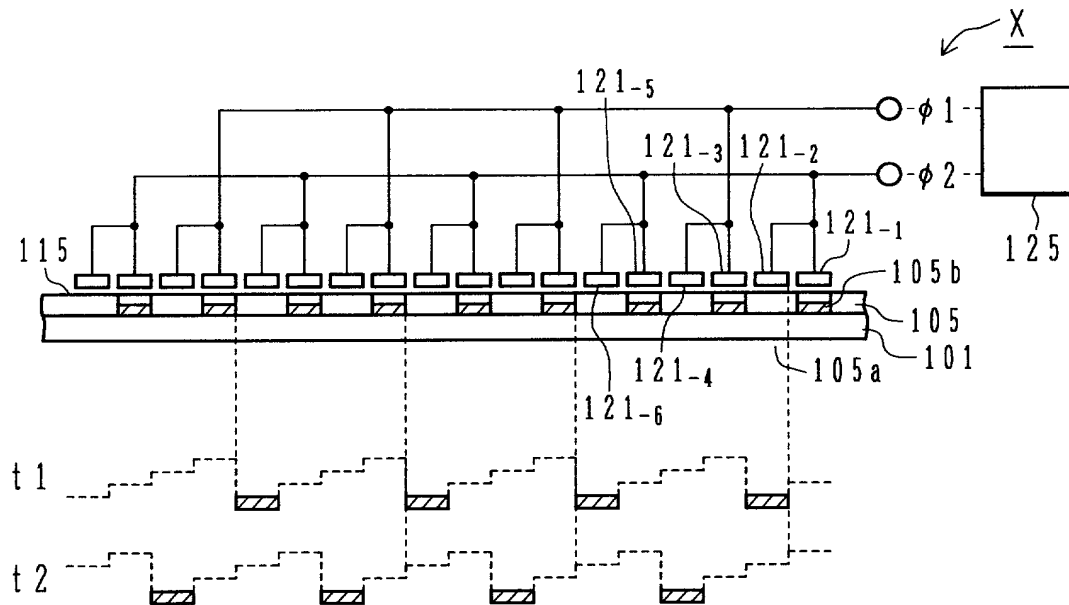


FIG.16
(PRIOR ART)

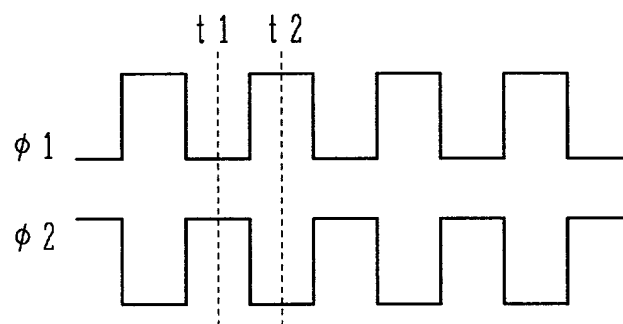
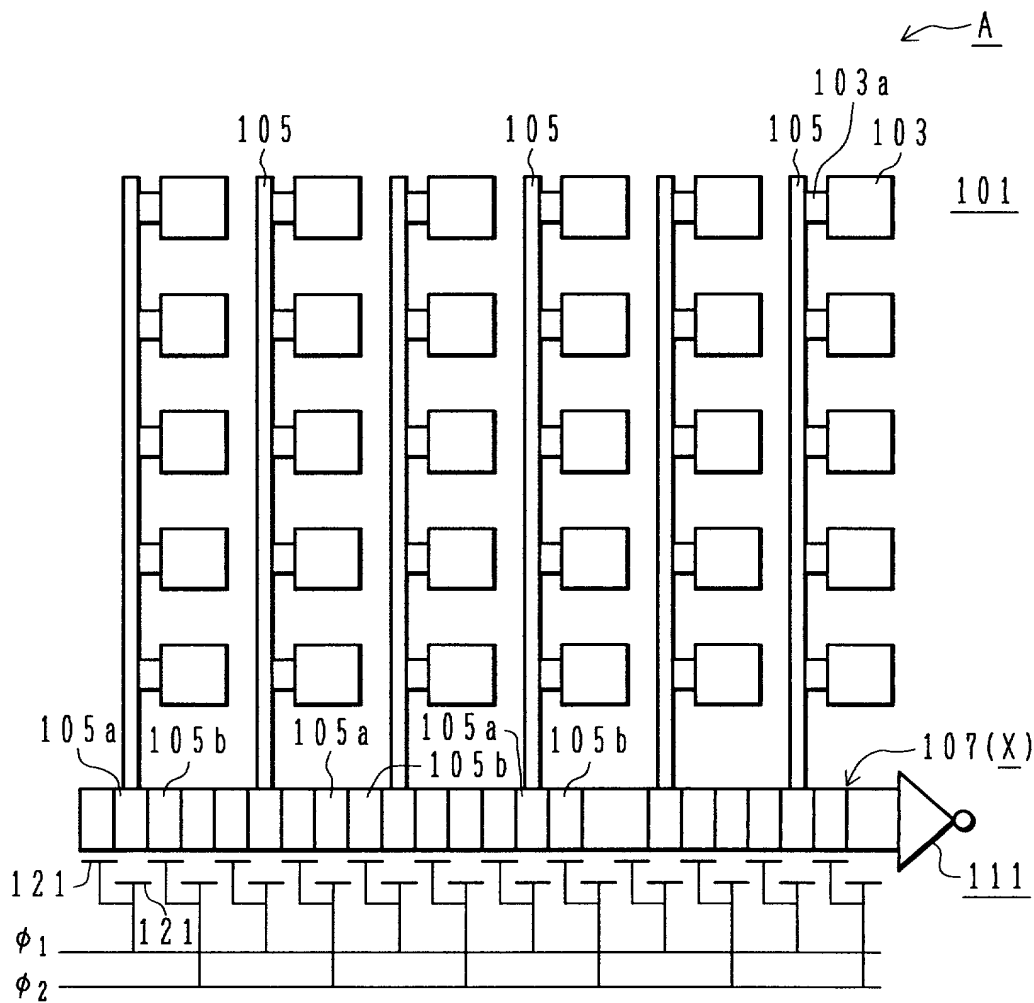


FIG.17
(PRIOR ART)



Declaration and Power of Attorney For Patent Application

特許出願宣言書及び委任状

Japanese Language Declaration

日本語宣言書

下記の氏名の発明者として、私は以下の通り宣言します。

As a below named inventor, I hereby declare that:

私の住所、私書箱、国籍は下記の私の氏名の後に記載された通りです。

My residence, post office address and citizenship are as stated next to my name.

下記の名称の発明に関して請求範囲に記載され、特許出願している発明内容について、私が最初かつ唯一の発明者（下記の氏名が一つの場合）もしくは最初かつ共同発明者であると（下記の名称が複数の場合）信じています。

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

CHARGE TRANSFER DEVICE, SOLID STATE IMAGE PICKUP DEVICE USING

CHARGE TRANSFER DEVICE, AND CONTROL METHOD FOR SOLID STATE IMAGE PICKUP DEVICE

上記発明の明細書（下記の欄で×印がついていない場合は、本書に添付）は、

the specification of which is attached hereto unless the following box is checked:

☐ 月 日に提出され、米国出願番号または特許協定条約国際出願番号を _____ とし、
（該当する場合） _____ に訂正されました。

☐ was filed on _____
as United States Application Number or
PCT International Application Number
_____ and was amended on _____
(if applicable).

私は、特許請求範囲を含む上記訂正後の明細書を検討し、内容を理解していることをここに表明します。

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

私は、連邦規則法典第37編第1条56項に定義されたとおり、特許資格の有無について重要な情報を開示する義務があることを認めます。

I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, Section 1.56.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

Japanese Language Declaration (日本語宣言書)

私は、米国法典第35編119条(a)-(d)項又は365条(b)項に基づき下記の、米国以外の国の少なくとも一ヶ国を指定している特許協定条約365(a)項に基づき国際出願、又は外国での特許出願もしくは発明者証の出願についての外国優先権をここに主張するとともに、優先権を主張している、本出願の前に出願された特許または発明者証の外国出願を以下に、枠内をマークすることで、示しています。

Prior Foreign Application(s)

外国での先行出願

He111-287337

Japan

(Number)

(Country)

(番号)

(国名)

2000-287486

Japan

(Number)

(Country)

(番号)

(国名)

私は、第35編米国法典119条(e)項に基づいて下記の米国特許出願規定に記載された権利をここに主張いたします。

(Application No.)

(出願番号)

(Filing Date)

(出願日)

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(Application No.)

(出願番号)

(Filing Date)

(出願日)

(Application No.)

(出願番号)

(Filing Date)

(出願日)

私は、私自身の知識に基づいて本宣言書中で私が行なう表明が真実であり、かつ私の入手した情報と私の信じることに基づき表明が全て真実であると信じていること、さらに故意になされた虚偽の表明及びそれと同等の行為は米国法典第18編第1001条に基づき、罰金または拘禁、もしくはその両方により処罰されること、そしてそのような故意による虚偽の表明を行なえば、出願した、又は既に許可された特許の有効性が失われることを認識し、よってここに上記のごとく宣誓を致します。

I hereby claim foreign priority under Title 35, United States Code, Section 119 (a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed.

Priority Not Claimed

優先権主張なし

07/10/99

(Day/Month/Year Filed)

(出願年月日)

21/09/00

(Day/Month/Year Filed)

(出願年月日)

I hereby claim the benefit under Title 35, United States Code, Section 119(e) of any United States provisional application(s) listed below.

(Application No.)

(出願番号)

(Filing Date)

(出願日)

I hereby claim the benefit under Title 35, United States Code, Section 120 of any United States application(s), or 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of Title 35, United States Code Section 112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, Section 1.56 which became available between the filing date of the prior application and the national or PCT International filing date of application.

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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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POWER OF ATTORNEY: As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith (list name and registration number)

特許送付元

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